

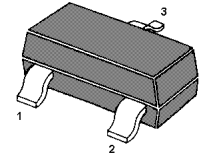
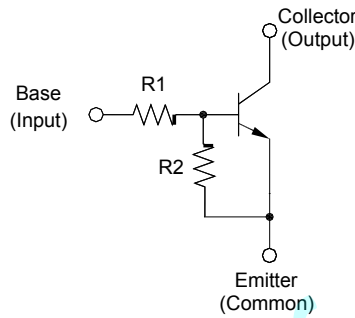
MMBTRC241S...MMBTRC246S

NPN Silicon Epitaxial Planar Transistor

for high current switching, interface circuit and driver circuit application.

Feature

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- High output current



1- Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Resistor Values

Type	R1 (KΩ)	R2 (KΩ)
MMBTRC241S	1	1
MMBTRC242S	2.2	2.2
MMBTRC243S	4.7	4.7
MMBTRC244S	10	10
MMBTRC245S	1	10
MMBTRC246S	2.2	10

Absolute Maximum Ratings (T_a = 25 °C)

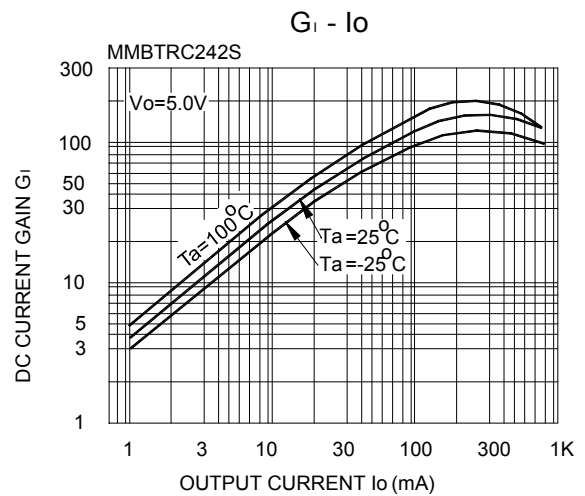
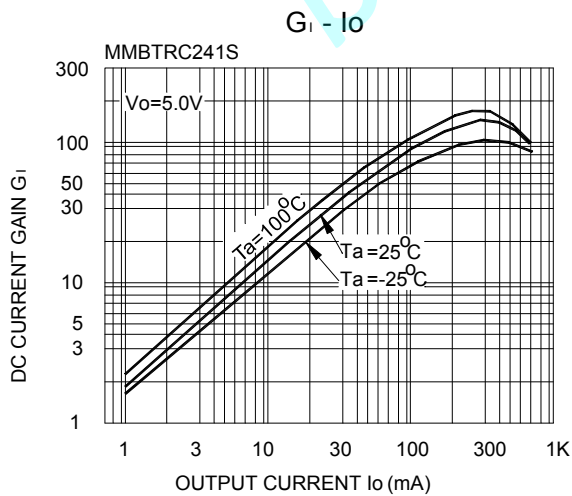
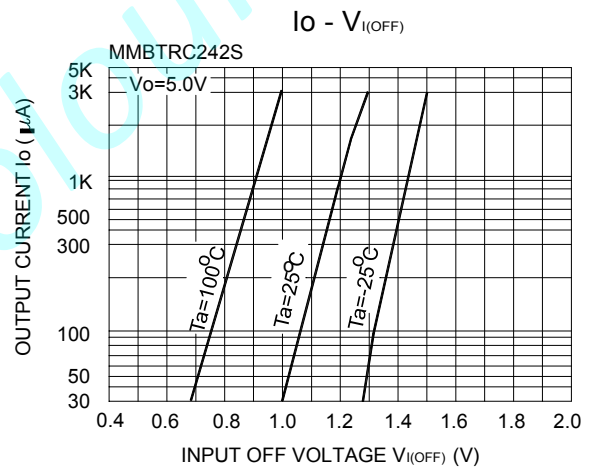
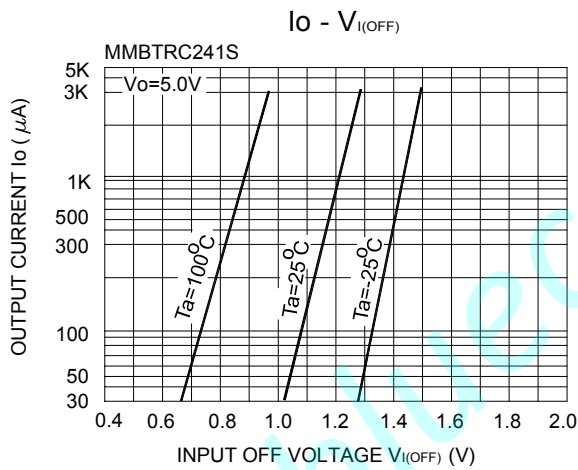
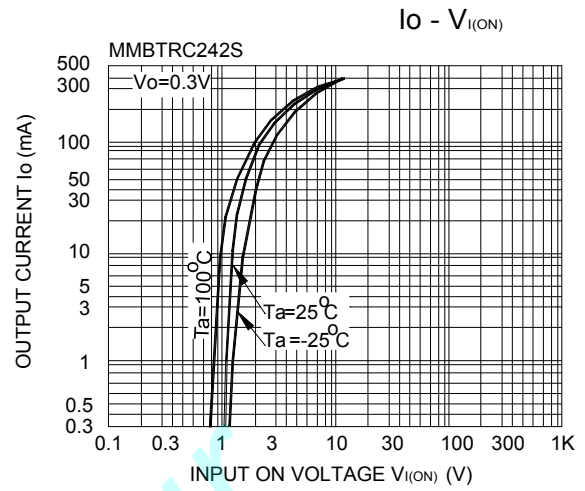
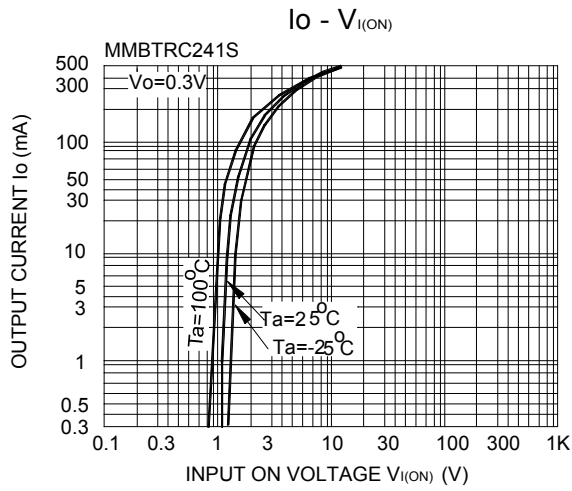
Parameter		Symbol	Value	Unit
Output Voltage		V _o	50	V
Input Voltage	MMBTRC241S	V _i	10, -10	V
	MMBTRC242S		12, -10	
	MMBTRC243S		20, -10	
	MMBTRC244S		30, -10	
	MMBTRC245S		10, -5	
	MMBTRC246S		12, -6	
Output Current		I _o	800	mA
Total Power Dissipation		P _{tot}	200	mW
Junction Temperature		T _j	150	°C
Storage Temperature Range		T _{stg}	- 55 to + 150	°C

Characteristics at $T_a = 25^\circ\text{C}$

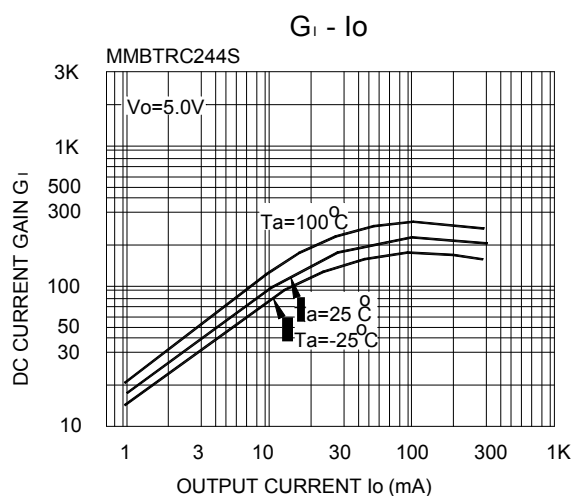
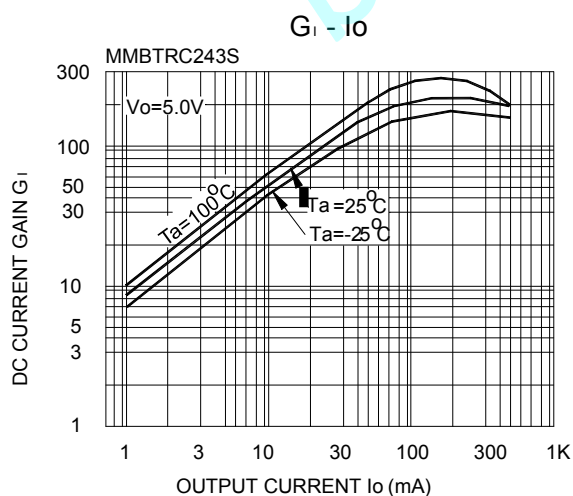
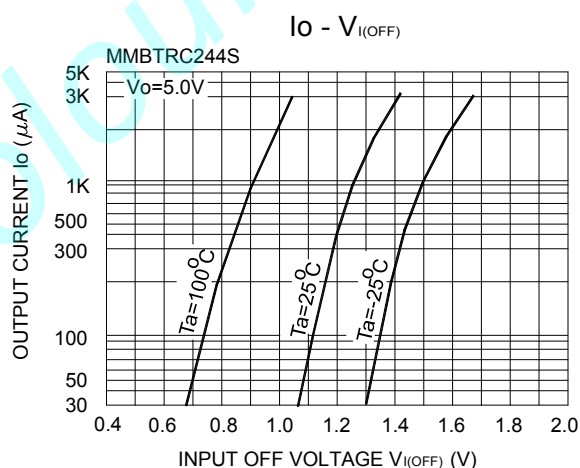
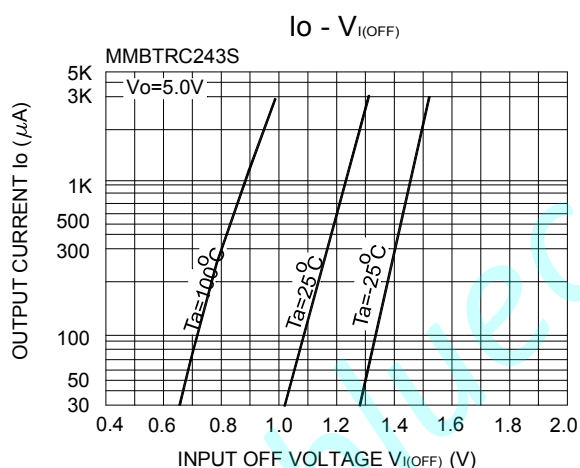
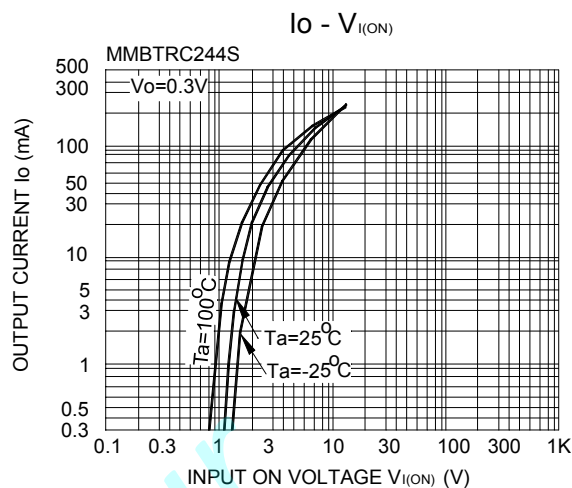
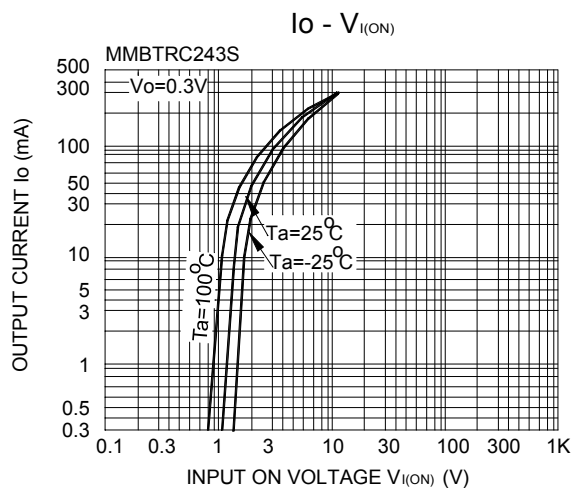
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_O = 5\text{ V}$, $I_O = 50\text{ mA}$	MMBTRC241S	33	-	-	-
	MMBTRC242S	39	-	-	-
	MMBTRC243S	47	-	-	-
	MMBTRC244S	56	-	-	-
	MMBTRC245S	56	-	-	-
	MMBTRC246S	56	-	-	-
Output Cutoff Current at $V_O = 30\text{ V}$	$I_{O(OFF)}$	-	-	10	μA
Input Current at $V_I = 5\text{ V}$	MMBTRC241S	-	-	7.2	mA
	MMBTRC242S	-	-	3.8	
	MMBTRC243S	-	-	1.8	
	MMBTRC244S	-	-	0.88	
	MMBTRC245S	-	-	7.2	
	MMBTRC246S	-	-	3.6	
Output Voltage at $I_O = 50\text{ mA}$, $I_I = 2.5\text{ mA}$	$V_{O(ON)}$	-	-	0.3	V
Input Voltage (ON) at $V_O = 0.3\text{ V}$, $I_O = 20\text{ mA}$	MMBTRC241S	-	-	3	V
	MMBTRC242S	-	-	3	
	MMBTRC243S	-	-	3	
	MMBTRC244S	-	-	3	
	MMBTRC245S	-	-	3	
	MMBTRC246S	-	-	2	
Input Voltage (OFF) at $V_O = 5\text{ V}$, $I_O = 0.1\text{ mA}$	MMBTRC241S~244S	$-V_{I(OFF)}$	0.5	-	V
	MMBTRC245S~246S		0.3	-	
Transition Frequency at $V_O = 10\text{ V}$, $I_O = 5\text{ mA}$, $f = 100\text{ MHz}$	$f_T^{1)}$	-	200	-	MHz

1) Characteristic of transistor only.

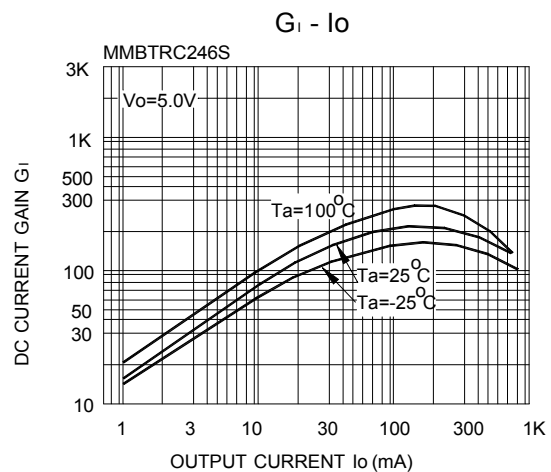
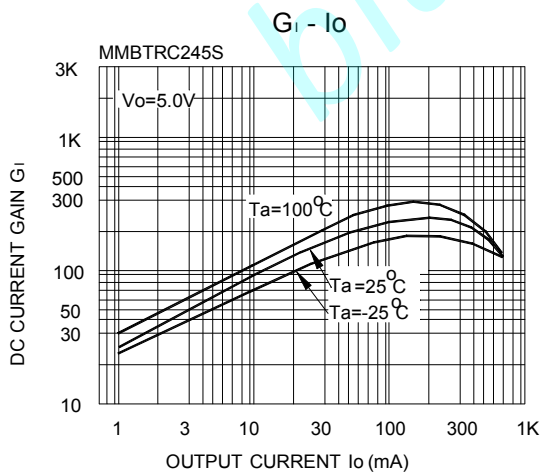
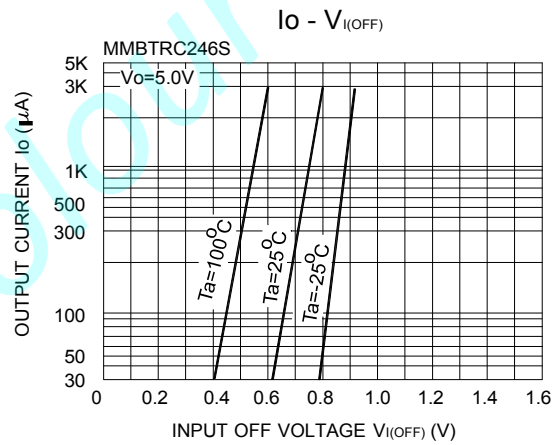
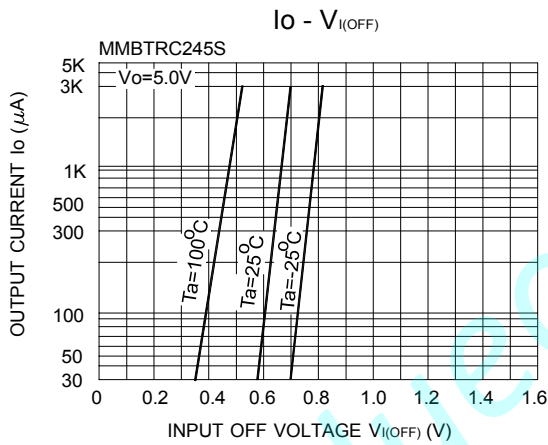
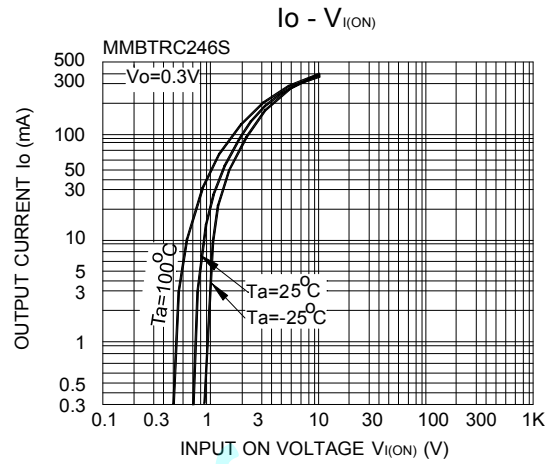
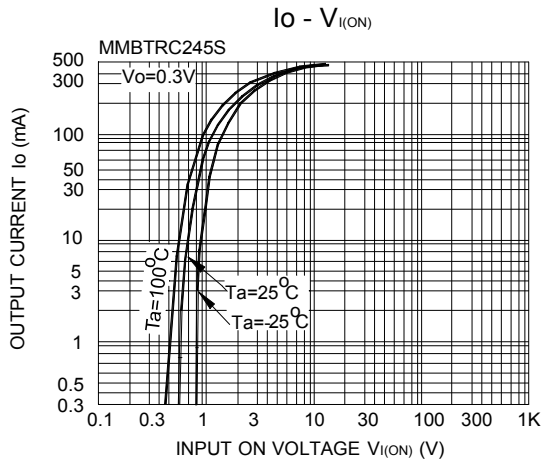
Typical Characteristics



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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

